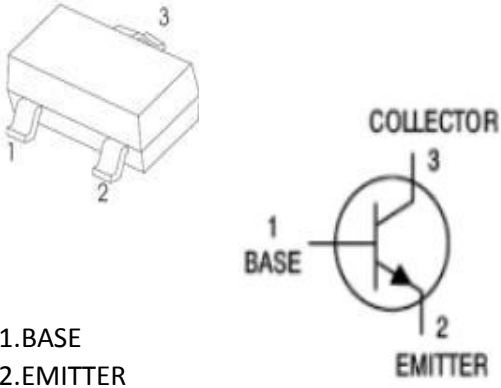


<b>TRANSISTOR (NPN)</b>	<b>SOT-23 Plastic-Encapsulate Transistors</b>																																						
<p><u>SOT-23</u></p>  <p>1.BASE 2.EMITTER 3.COLLECTOR</p> <p>Marking :2X</p>	<p><b>Features</b></p> <ul style="list-style-type: none"> <li>※ Complimentary to MMBT4403</li> <li>※ Collector Current: <math>I_c=0.6A</math></li> <li>※ Switching Transistor</li> </ul>																																						
<p><b>MAXIMUM RATINGS (Ta=25°C unless otherwise noted)</b></p> <table border="1"> <thead> <tr> <th>Parameter</th> <th>Symbol</th> <th>Value</th> <th>Unit</th> </tr> </thead> <tbody> <tr> <td>Collector-Base Voltage</td> <td>VCBO</td> <td>60</td> <td>V</td> </tr> <tr> <td>Collector-Emitter Voltage</td> <td>VCEO</td> <td>40</td> <td>V</td> </tr> <tr> <td>Emitter-Base Voltage</td> <td>VEBO</td> <td>6</td> <td>V</td> </tr> <tr> <td>Collector Current</td> <td>IC</td> <td>600</td> <td>mA</td> </tr> <tr> <td>Collector Power Dissipation</td> <td>PC</td> <td>250</td> <td>mW</td> </tr> <tr> <td>Thermal Resistance From Junction To Ambient</td> <td>RθJA</td> <td>417</td> <td>°C/W</td> </tr> <tr> <td>Junction Temperature</td> <td>Tj</td> <td>150</td> <td>°C</td> </tr> <tr> <td>Storage Temperature</td> <td>Tstg</td> <td>-55~+150</td> <td>°C</td> </tr> </tbody> </table>				Parameter	Symbol	Value	Unit	Collector-Base Voltage	VCBO	60	V	Collector-Emitter Voltage	VCEO	40	V	Emitter-Base Voltage	VEBO	6	V	Collector Current	IC	600	mA	Collector Power Dissipation	PC	250	mW	Thermal Resistance From Junction To Ambient	RθJA	417	°C/W	Junction Temperature	Tj	150	°C	Storage Temperature	Tstg	-55~+150	°C
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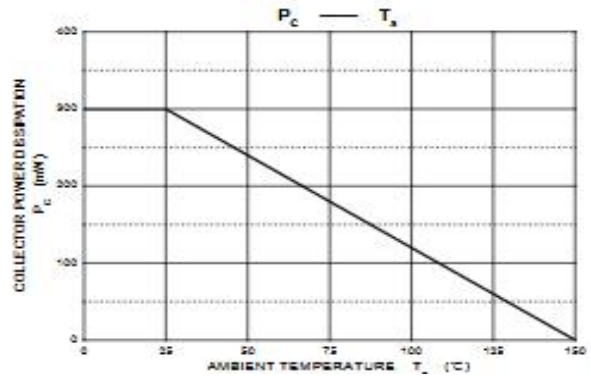
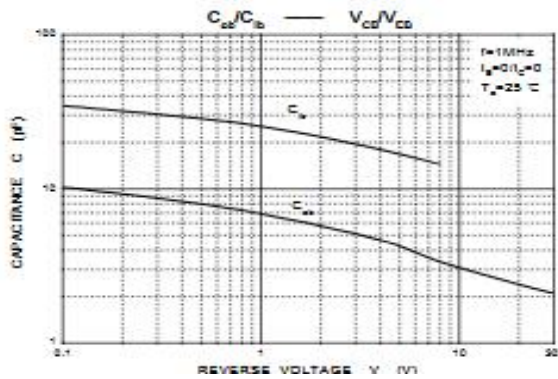
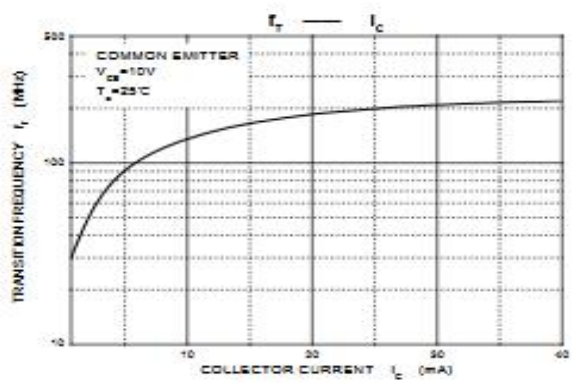
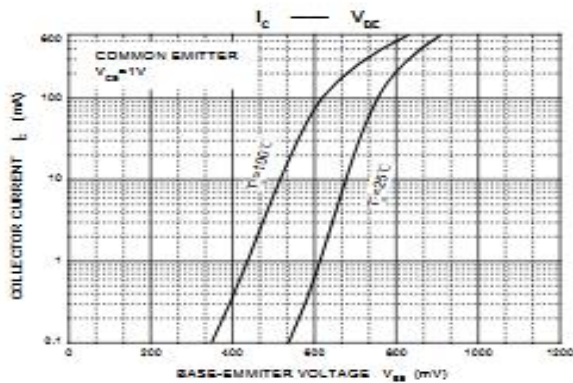
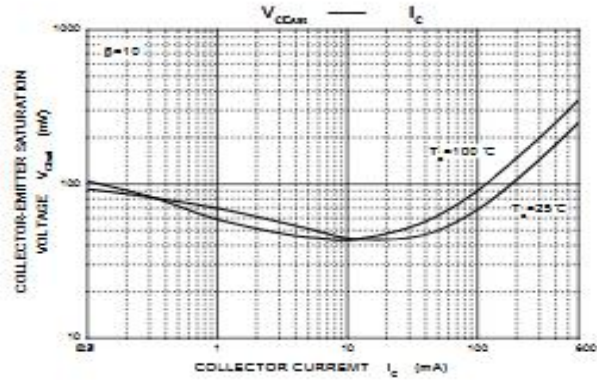
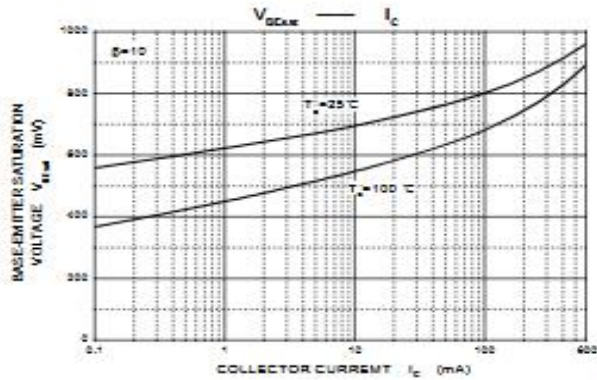
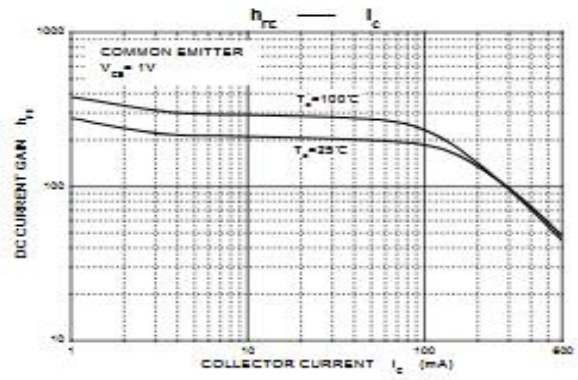
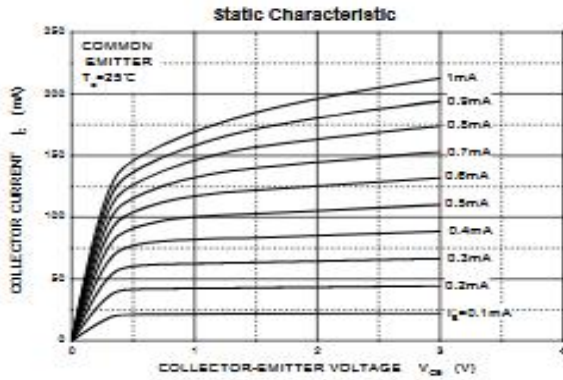
### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100µA, IE=0	60		200	V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	40		100	V
Emitter-base breakdown voltage	V(BR)EBO	IE= 100µA, IC=0	6		30	V
Collector cut-off current	ICBO	VCB= 60 V , IE=0			0.1	µA
Collector cut-off current	ICEO	VCB= 40V , IE=0			0.1	µA
Emitter cut-off current	IEBO	VEB= 6V , IC=0			0.1	µA
DC current gain	hFE	VCE=5V, IC= 1mA	100		300	
	hFE	VCE=5V, IC= 10mA	80			
	hFE	VCE=5V, IC= 100mA	60			
Collector-emitter saturation voltage	VCE(sat)	IC=500 mA, IB= 50mA			1	V
Base-emitter saturation voltage	VBE(sat)	IC=500 mA, IB= 50mA			2	V
Transition frequency	fT	VCE=20V, IC= 100mA f=100MHz	250			MHz
Delay time	td	VCC=3V, VBE=0.5V, IC=10mA, IB=1mA,			15	ns
Rise time	tr	VCC=3V, VBE=0.5V, IC=10mA, IB=1mA,			20	ns
Storage time	ts	VCC=3V, VBE=0.5V, IC=10mA, IB=1mA,			225	ns
Fall time	tf	VCC=3V, VBE=0.5V, IC=10mA, IB=1mA,			60	ns

### CLASSIFICATION OF HFE

<b>HFE</b>	<b>100-300</b>	
<b>Rank</b>	<b>L</b>	<b>H</b>
<b>Range</b>	<b>100-200</b>	<b>200-300</b>

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)